

AMENDMENTS TO THE SPECIFICATION:

Before the first paragraph beginning on line 3 of page 1, please insert the following new paragraph:

This application is a divisional of Application No. 09/469,300, filed on December 22, 1999, which is incorporated herein by reference.

Please replace the paragraph beginning on page 2, line 3 and ending on page 2, line 16, with the following amended paragraph:

Aluminum and aluminum alloys are commonly used for walls of plasma reactors. In order to prevent corrosion of the walls, various techniques have been proposed for coating the aluminum surface with various coatings. For instance, U.S. Patent No. 5,641,375 discloses that aluminum chamber walls have been anodized to reduce plasma erosion and wear of the walls. The '375 patent states that eventually the anodized layer is sputtered or etched off and the chamber must be replaced. U.S. Patent No. 5,680,013 states that a technique for flame spraying Al_2O_3 on metal surfaces of an etching chamber is disclosed in U.S. Patent No. 4,491,496. The '013 patent states that the differences in thermal expansion coefficients between aluminum and ceramic coatings such as aluminum oxide leads to cracking of the coatings due to thermal cycling and eventual failure of the coatings in corrosive environments. U.S. Patent No. 5,085,727 discloses a carbon coating for walls of a plasma chamber wherein the coating is deposited by plasma assisted CVD.[.]

Please replace the paragraphs beginning on page 3, line 10 and ending on page 3, line 23, with the following amended paragraphs:

In addition to the above, the use of silicon carbide in semiconductor processing equipment is disclosed in U.S. Patent Nos. 4,401,689 (susceptor tube), 4,518,349 (furnace support rod), 4,999,228 (diffusion tube), 5,074,456 (upper electrode), 5,252,892 (plasma cathode chamber), 5,460,684 (resistive layer of ESC), ~~5,463,524~~ 5,463,525 (sensing pin), 5,578,129 (filter plate of load lock system), 5,538,230 (wafer boat), 5,595,627 (upper electrode), 5,888,907 (electrode plate), and 5,892,236 (ion implantation device).

Other documents include Japanese Patent Publication Nos. ~~54-10825 (semiconductor diffusion oven material)~~; 60-200519 (susceptor), ~~61-284301 (upper electrode)~~; 63-35452 (diffusion oven tube, liner tube, port element, paddle), 63-186874 (microwave heated sample plate), 63-138737 (upper electrode of plasma etch reactor), 3-201322 (coating for part in vacuum environment), and 8-17745 (wafer heater). Of these, Japanese Patent Publication Nos. ~~No. 54-10825 and 63-35452 disclose~~ discloses parts made of slip cast silicon carbide.

Please replace the paragraph beginning on page 4, line 4 and ending on page 4, line 10, with the following amended paragraph:

In discussing the need for cleanliness and the elimination of contaminants in the processing of semiconductor wafers; U.S. Patent No. 5,538,230 references U.S. Patent

Nos. ~~3,951,541~~; 3,962,391; 4,093,201; 4,203,940; 4,761,134; 4,978,567; 4,987,016 and

Japanese Publication No. 50-90184. The '230 patent also references U.S. Patent Nos.

3,951,587 and 5,283,089 for discussions of SiC parts and references U.S. Patent No.

4,761,134 for a discussion of CVD SiC on Si infiltrated SiC or porous Si that has not been filled with Si.